IXYS

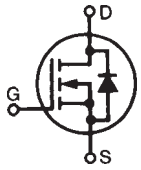
Advance Technical Information

TrenchT2™ Power MOSFET

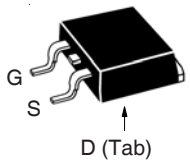
IXTA110N12T2
IXTP110N12T2

V_{DSS} = 120V
I_{D25} = 110A
$R_{DS(on)}$ ≤ 14mΩ

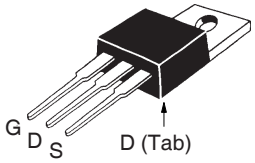
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



TO-263AA (IXTA)



TO-220AB (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	120	V
V_{DGR}	T_J = 25°C to 175°C, R_{GS} = 1MΩ	120	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	110	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	200	A
I_A	T_C = 25°C	55	A
E_{AS}	T_C = 25°C	800	mJ
P_D	T_C = 25°C	517	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g

Symbol (T_J = 25°C Unless Otherwise Specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	120			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5		4.5	V
I_{GSS}	V_{GS} = ± 20V, V_{DS} = 0V			±200	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			5	μA
	T_J = 150°C			350	μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.5 • I_{D25}, Notes 1, 2		11.4	14.0	mΩ

Features

- International Standard Packages
- 175°C Operating Temperature
- Avalanche Rated
- Low $R_{DS(on)}$
- Fast Intrinsic Rectifier
- High Current Handling Capability

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Synchronous Rectification
- DC/DC Converters and Off-Line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	46	78		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		6570		pF
C_{oss}			586		pF
C_{rss}			43		pF
$t_{d(on)}$	**Resistive Switching Times**		21		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		30		ns
$t_{d(off)}$	R_G = 2Ω (External)		29		ns
t_f			15		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		120		nC
Q_{gs}			36		nC
Q_{gd}			30		nC
R_{thJC}				0.29	°C/W
R_{thCH}	TO-220		0.50		°C/W

Source-Drain Diode

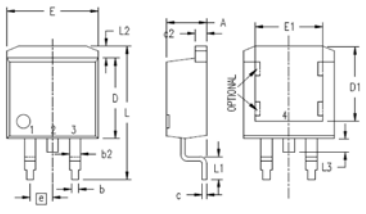
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			110	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			440	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 0.5 • I_{D25}, V_{GS} = 0V		64		ns
I_{RM}	-di/dt = 100A/μs		14.4		A
Q_{RM}	V_R = 60V		460		nC

Notes: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

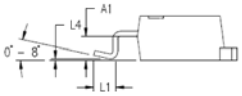
ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-263 Outline

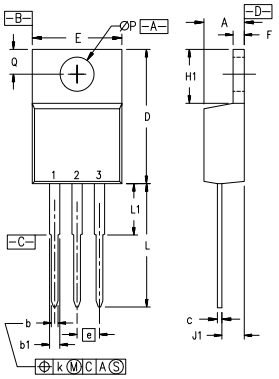


Pins:
1 - Gate
2,4 - Drain
3 - Source



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 Outline



Pins: 1 - Gate 2 - Drain
3 - Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Fig. 1. Output Characteristics @ T_J = 25°C

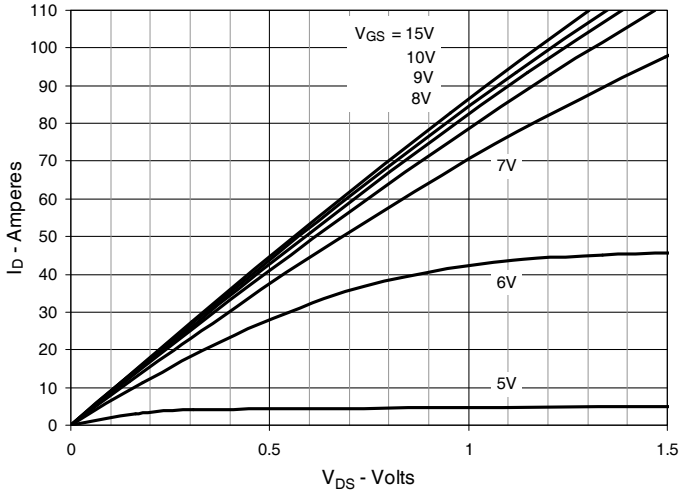


Fig. 2. Extended Output Characteristics @ T_J = 25°C

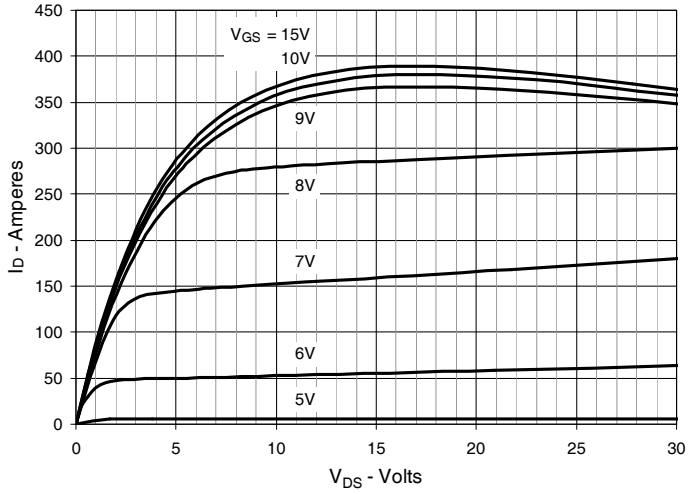


Fig. 3. Output Characteristics @ T_J = 150°C

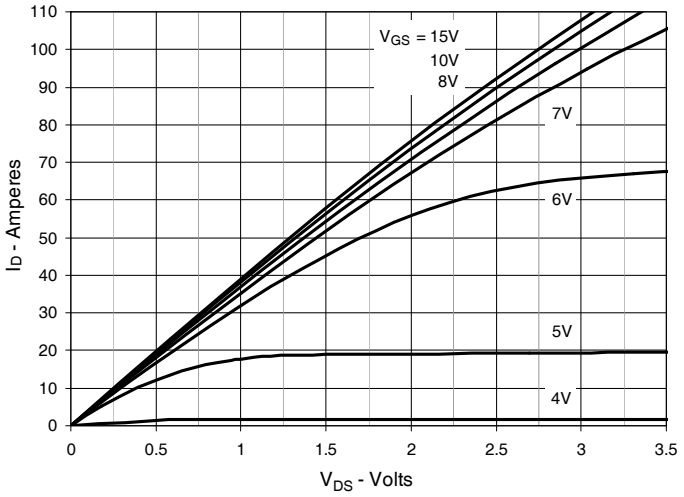


Fig. 4. Normalized $R_{DS(on)}$ to I_D = 55A Value vs. Junction Temperature

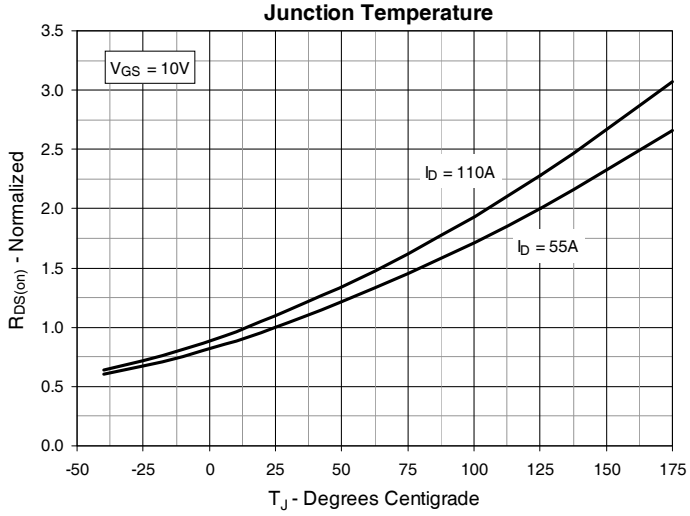


Fig. 5. Normalized $R_{DS(on)}$ to I_D = 55A vs. Drain Current

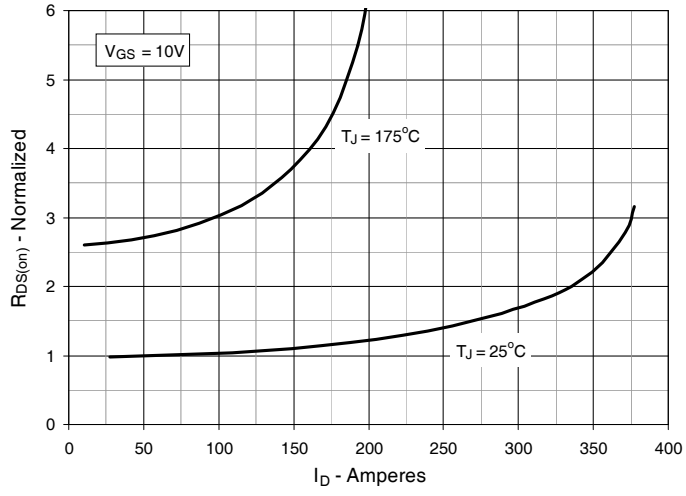


Fig. 6. Drain Current vs. Case Temperature

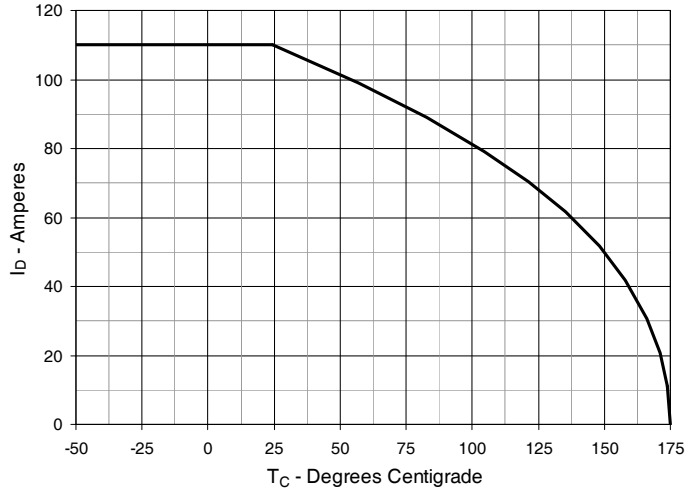


Fig. 7. Input Admittance

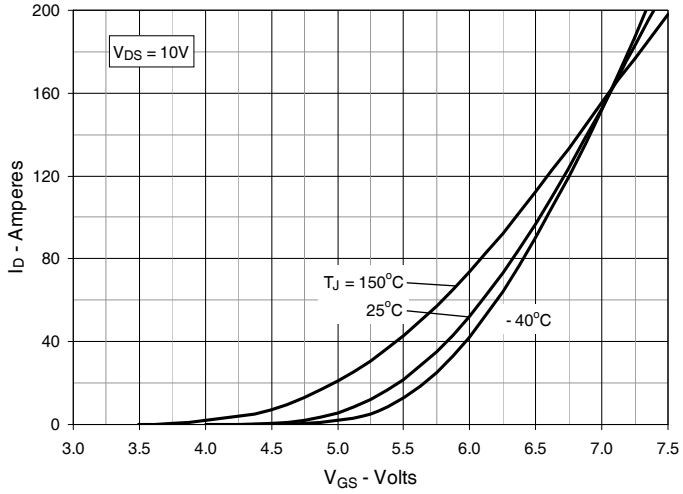


Fig. 8. Transconductance

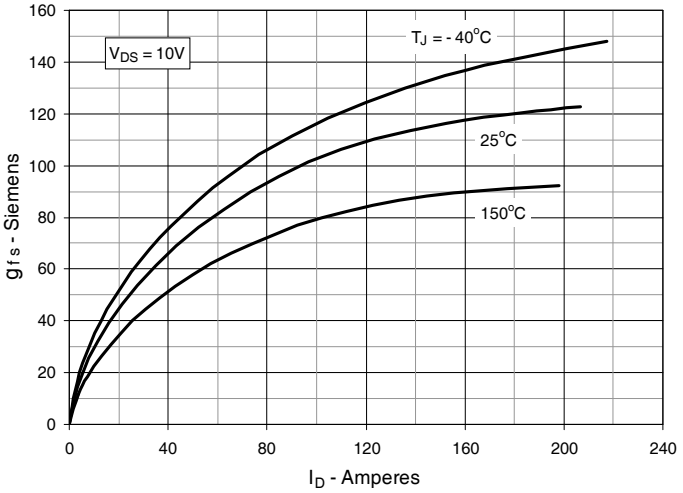


Fig. 9. Forward Voltage Drop of Intrinsic Diode

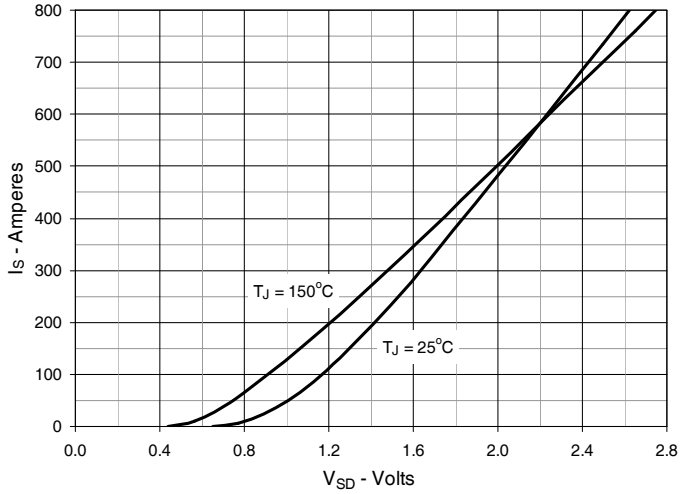


Fig. 10. Gate Charge

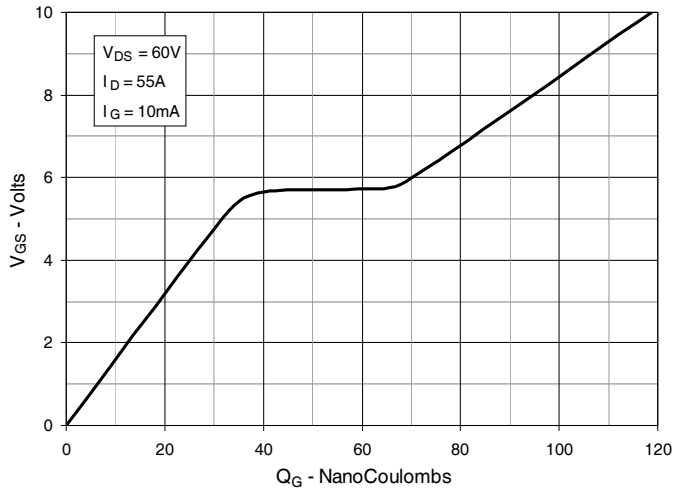


Fig. 11. Capacitance

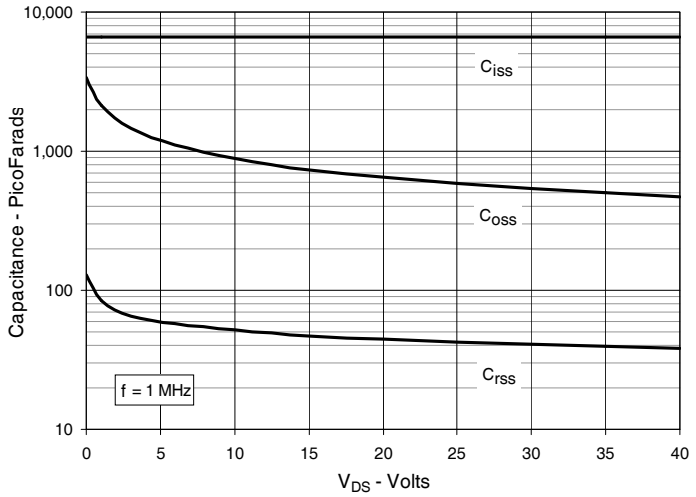


Fig. 12. Forward-Bias Safe Operating Area

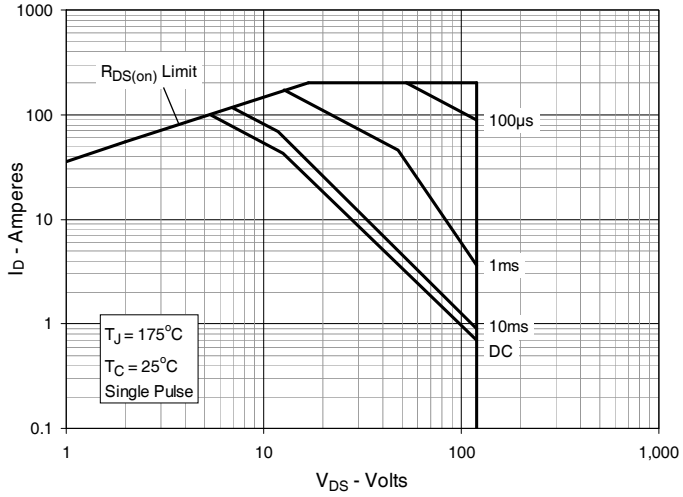


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

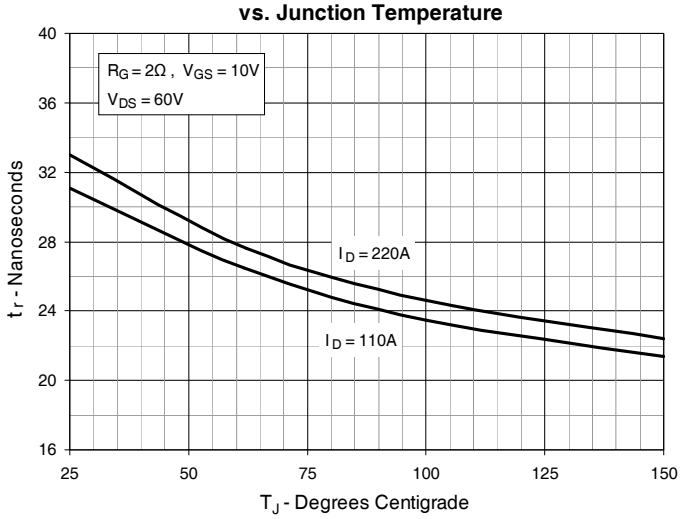


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

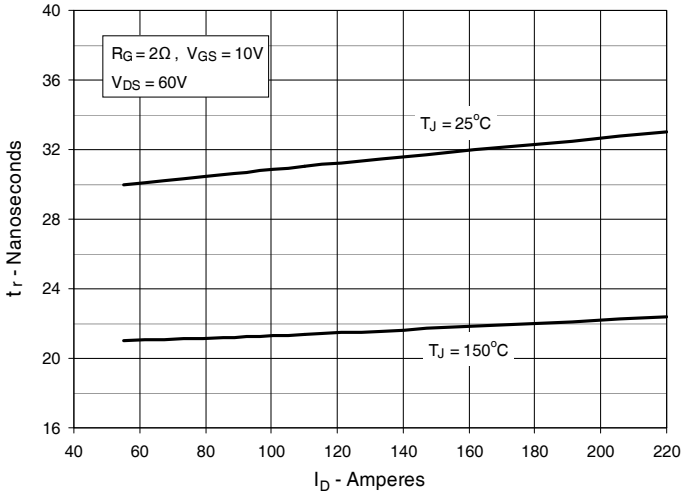


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

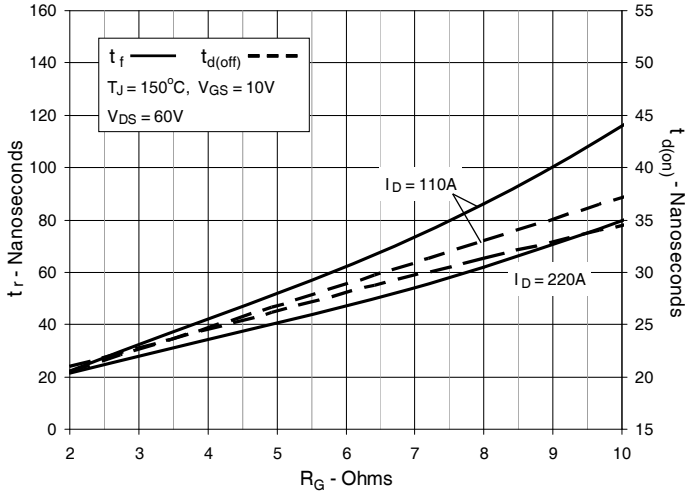


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

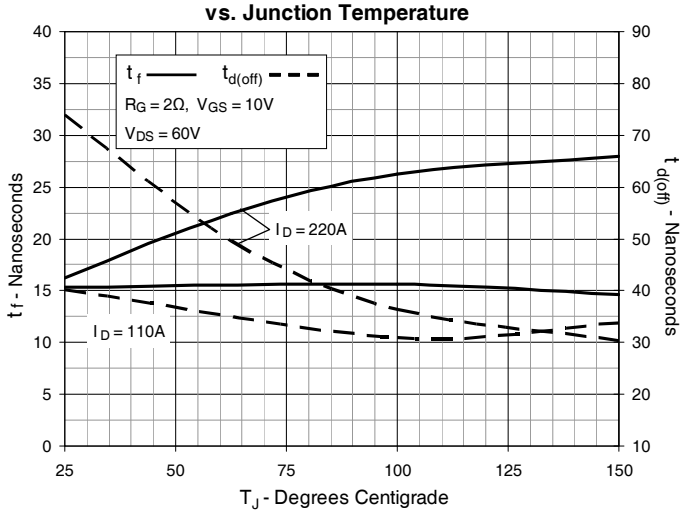


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

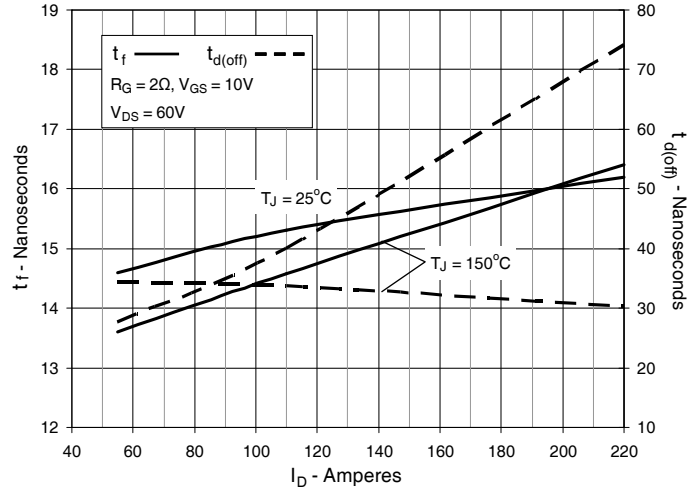


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

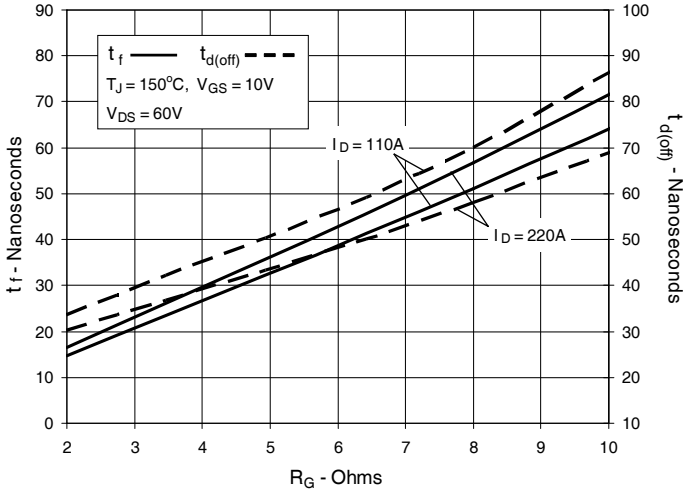


Fig. 19. Maximum Transient Thermal Impedance